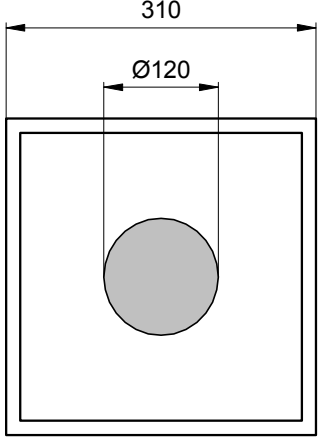


Radiation	Type	Technology	Electrodes
Red	Standard	AlInGaP/GaAs	P (anode) up

 <p style="text-align: center;">LED-02</p>	typ. dimensions (μm)
	<u>typ. thickness</u> 260 (±20) μm <u>cathode</u> gold alloy, 0.5 μm <u>anode</u> gold alloy, 1.5 μm

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.0	2.5	V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e		1.3		mW
Radiant power ²	I _F = 20 mA	Φ _e		2.5		mW
Luminous intensity ¹	I _F = 20 mA	I _V	55	70		mcd
Peak wavelength	I _F = 20 mA	λ _P	630	635	640	nm
Dominant wavelength	I _F = 20 mA	λ _D		626		nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		18		nm

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I _V (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-635-14-3				

Packing: Chips on adhesive film with wire-bond side on top